

# Micro-fabricated Ion Energy Analyzer\*

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- M. Blain, J. Stevens, J. Woodworth, *APL* 75 (1999) 3923;
- M. Sowa, M. Blain, R. Jarecki, J. Stevens, *APL* 80 (2002) 932.
- P. Kraus, T. Chua, C. Olsen, T. Bauer, *IEEE-NANO-2004* (Munich, Aug17-19, 2004).
- P. Kraus, T. Chua, et. al., 205<sup>th</sup> Meeting ECS (San Antonio, TX, May9-13, 2004).

**\*Work partially supported by SEMATECH**



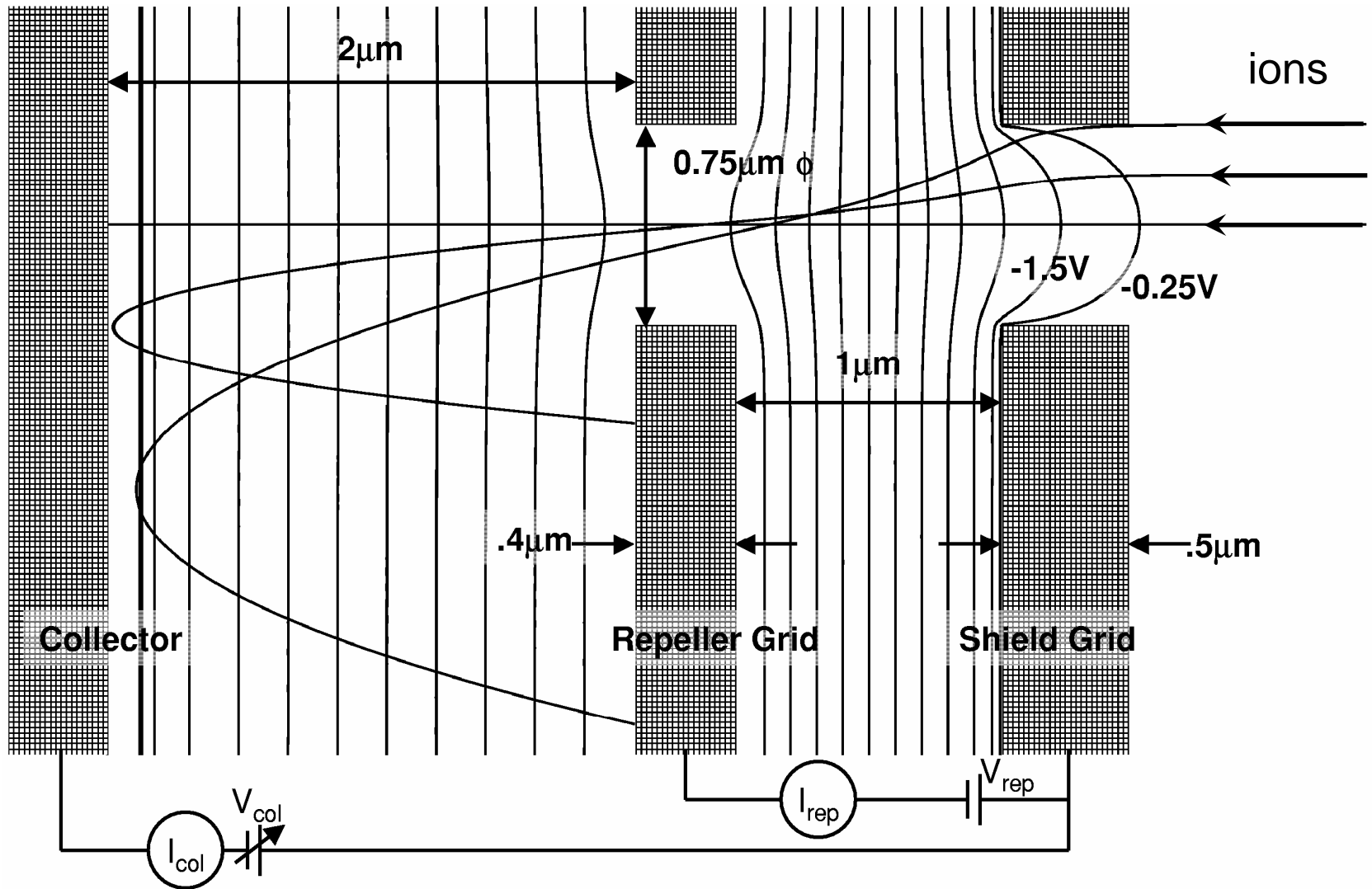
Goal: develop an ion diagnostic for plasmas used in semiconductor processing.

## Why Micro-fabricate Ion Energy Analyzer?

- Small size (can be put on top of a Si wafer)
- Nearly ideal hole alignment
- Very few ion - neutral collisions
- Good energy resolution in theory ( $\sim 0.2\%$ )



# modeling

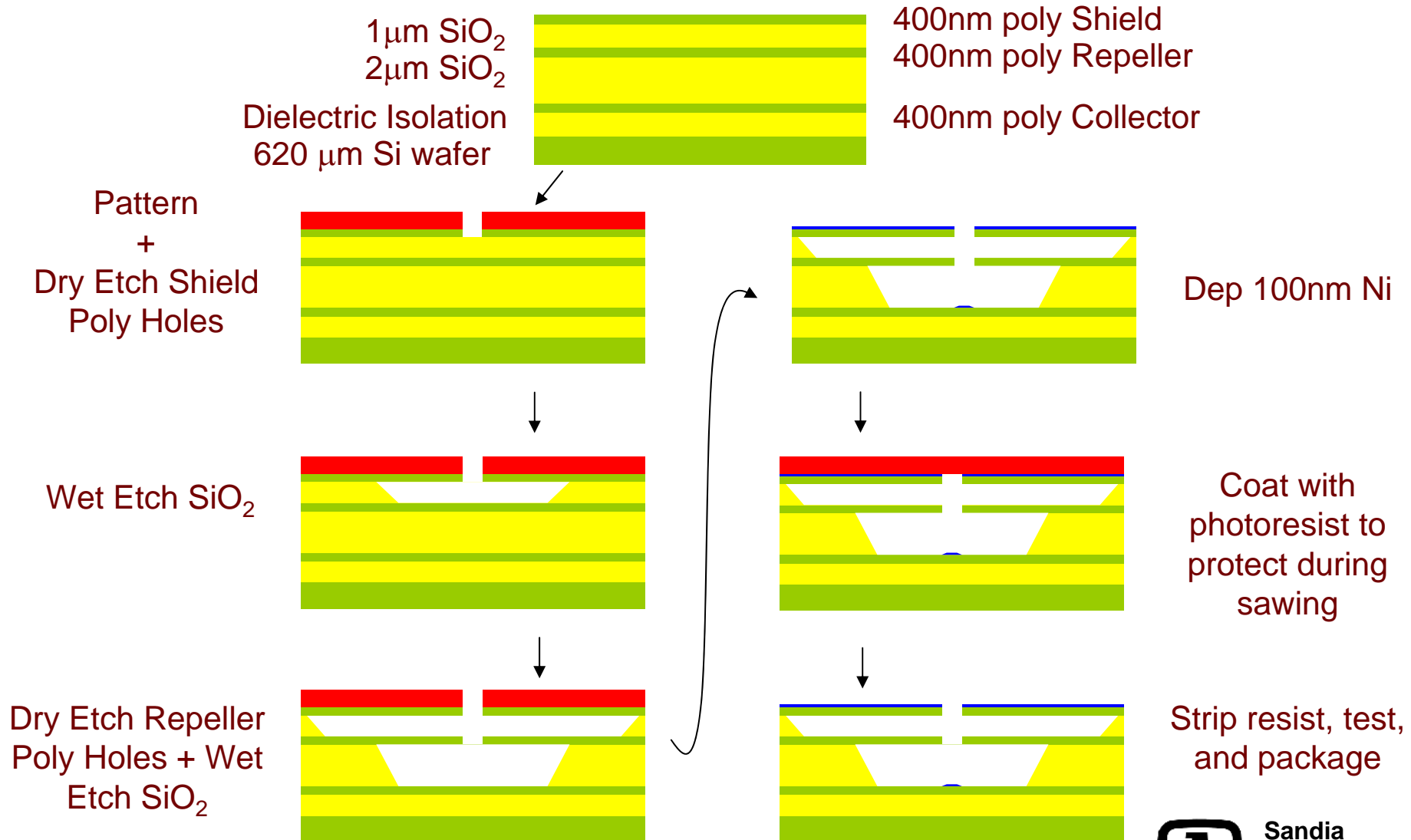


Typically there is 1 ion at a time in the analyzer.

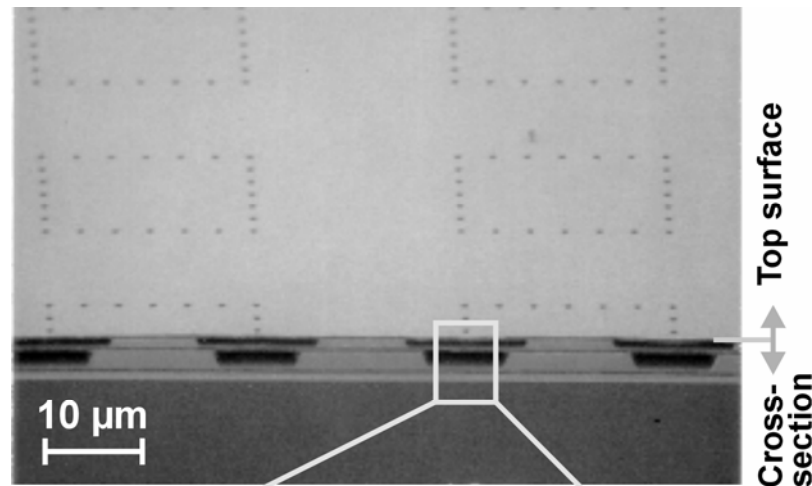
The collector should be able to resolve ion energy differences of  $<1\%$  at 50eV.



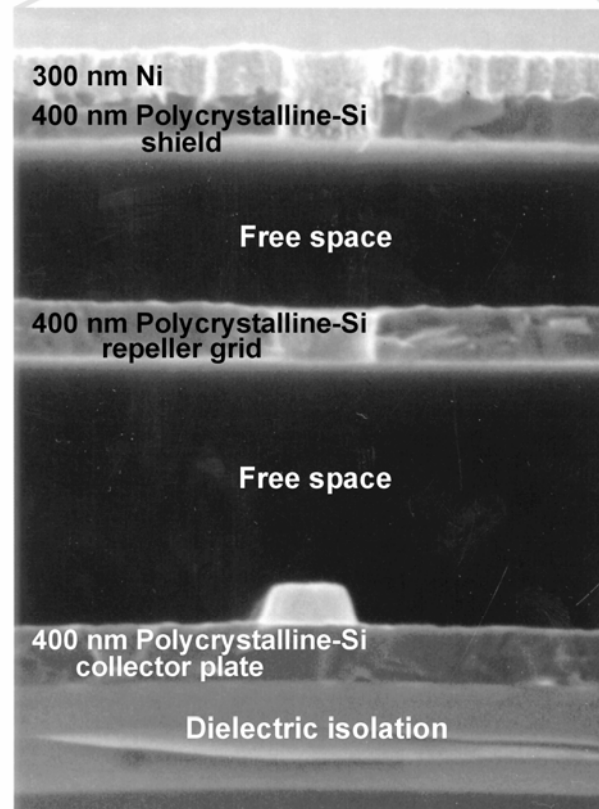
# Energy Analyzer Fabrication



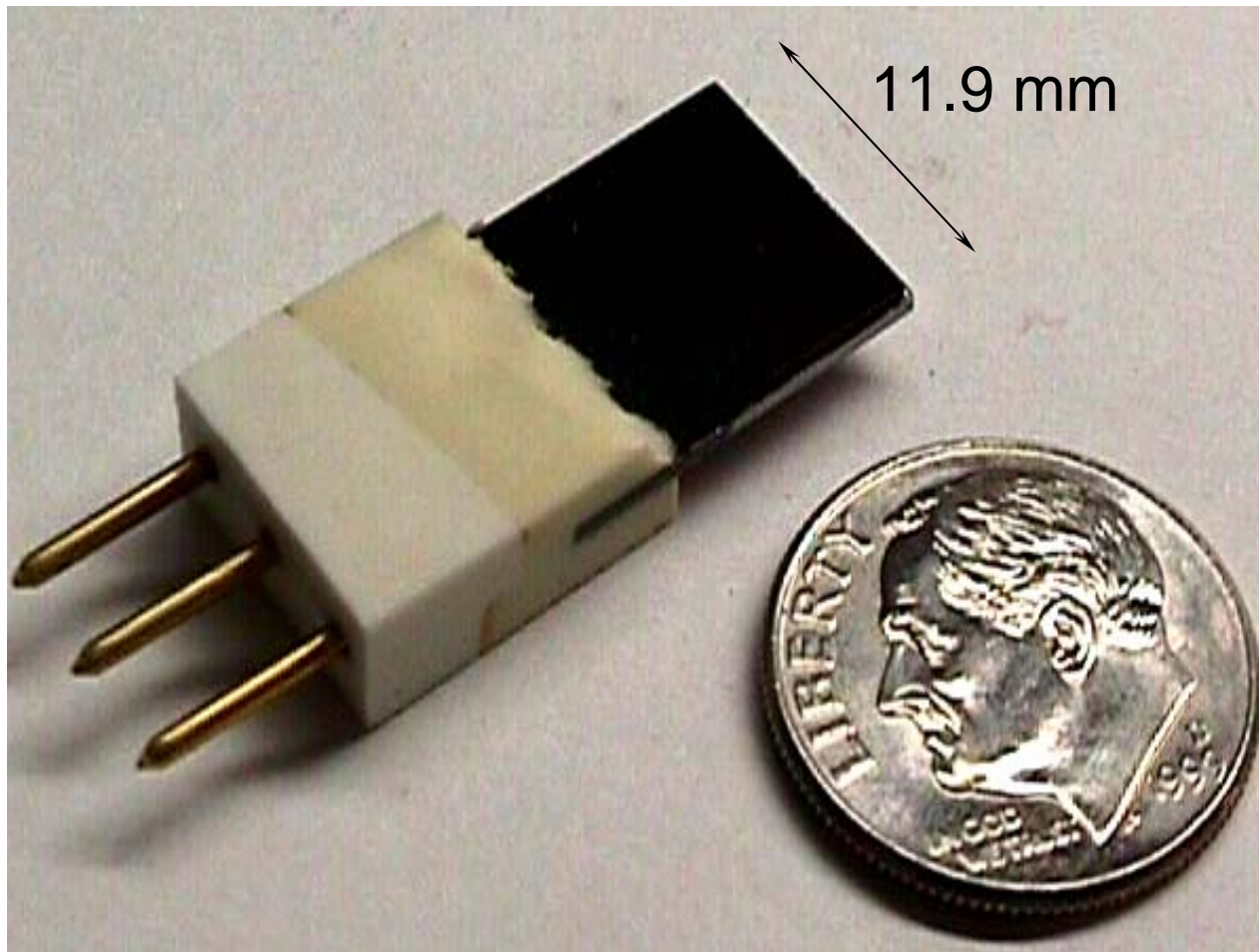
# SEM Images of IEA



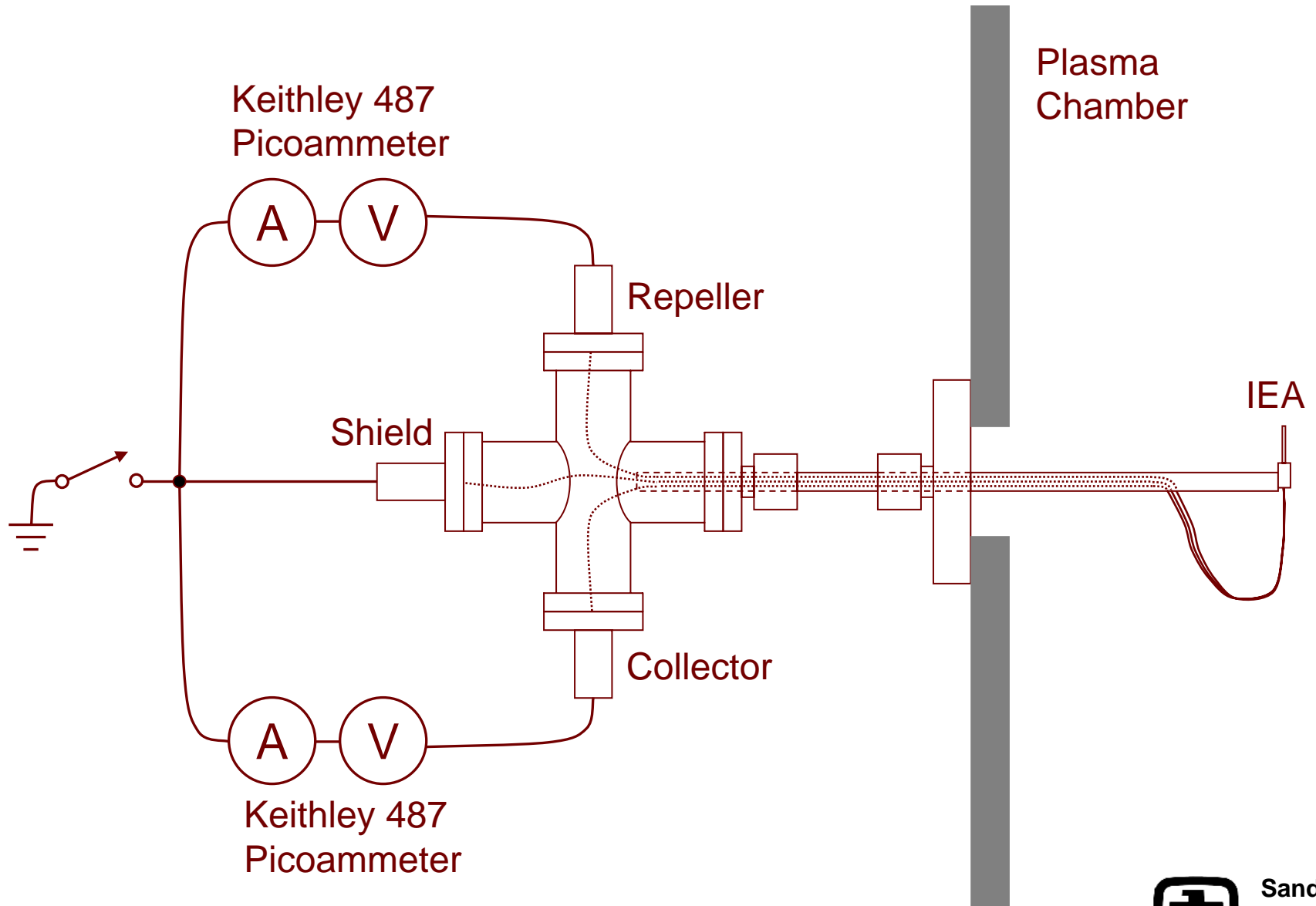
- 670,000 holes
- 0.5% open area



# Finished IEA



# Experimental Setup



# Experimental Setup on Test Stand





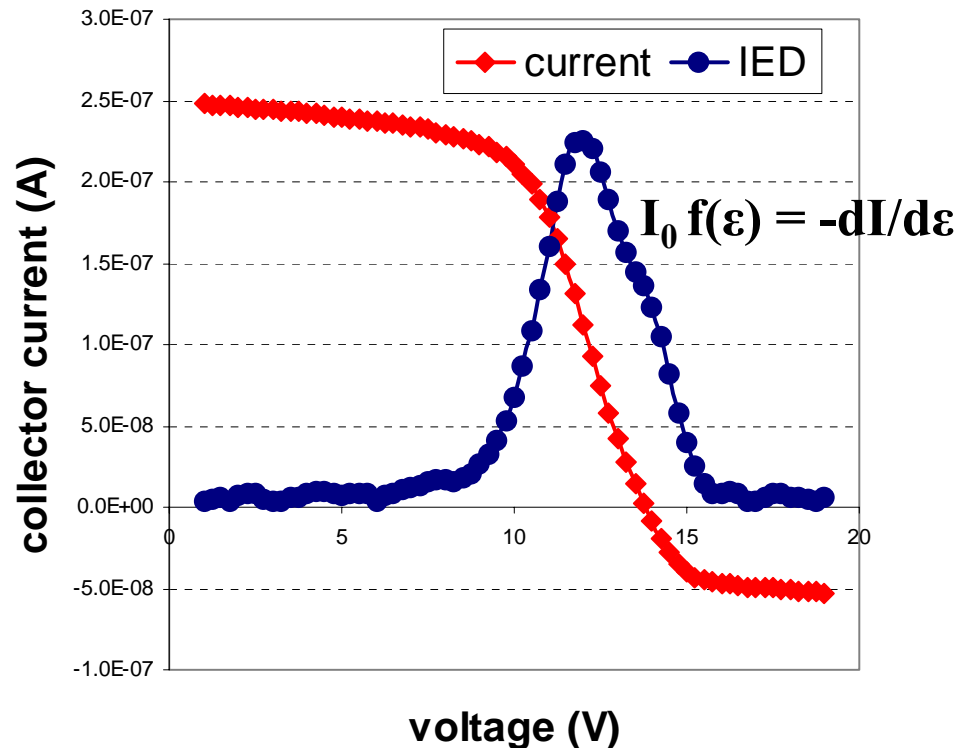
# Collector current & IED vs. voltage

## Process conditions:

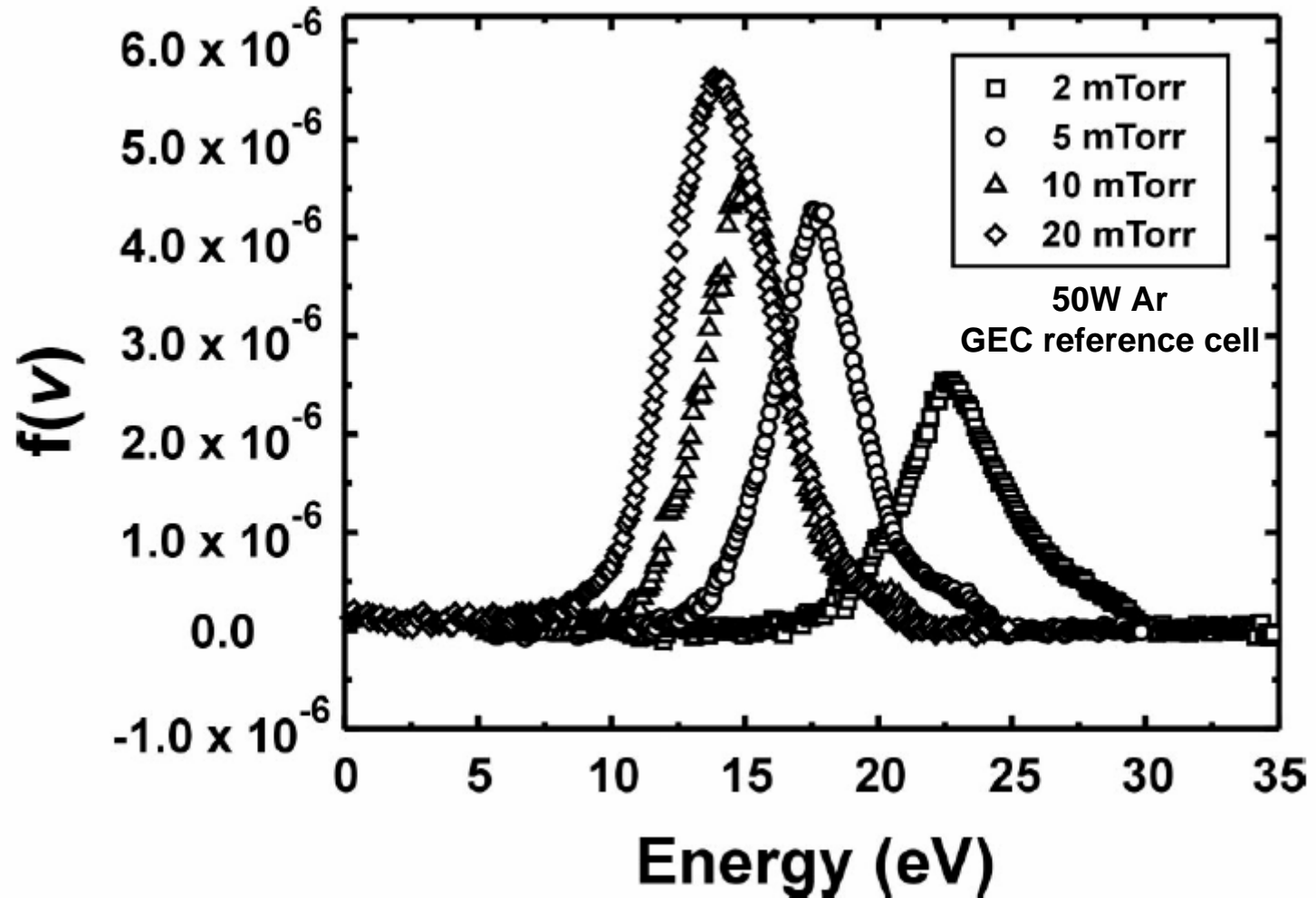
150 W RF power

10 mTorr N<sub>2</sub>

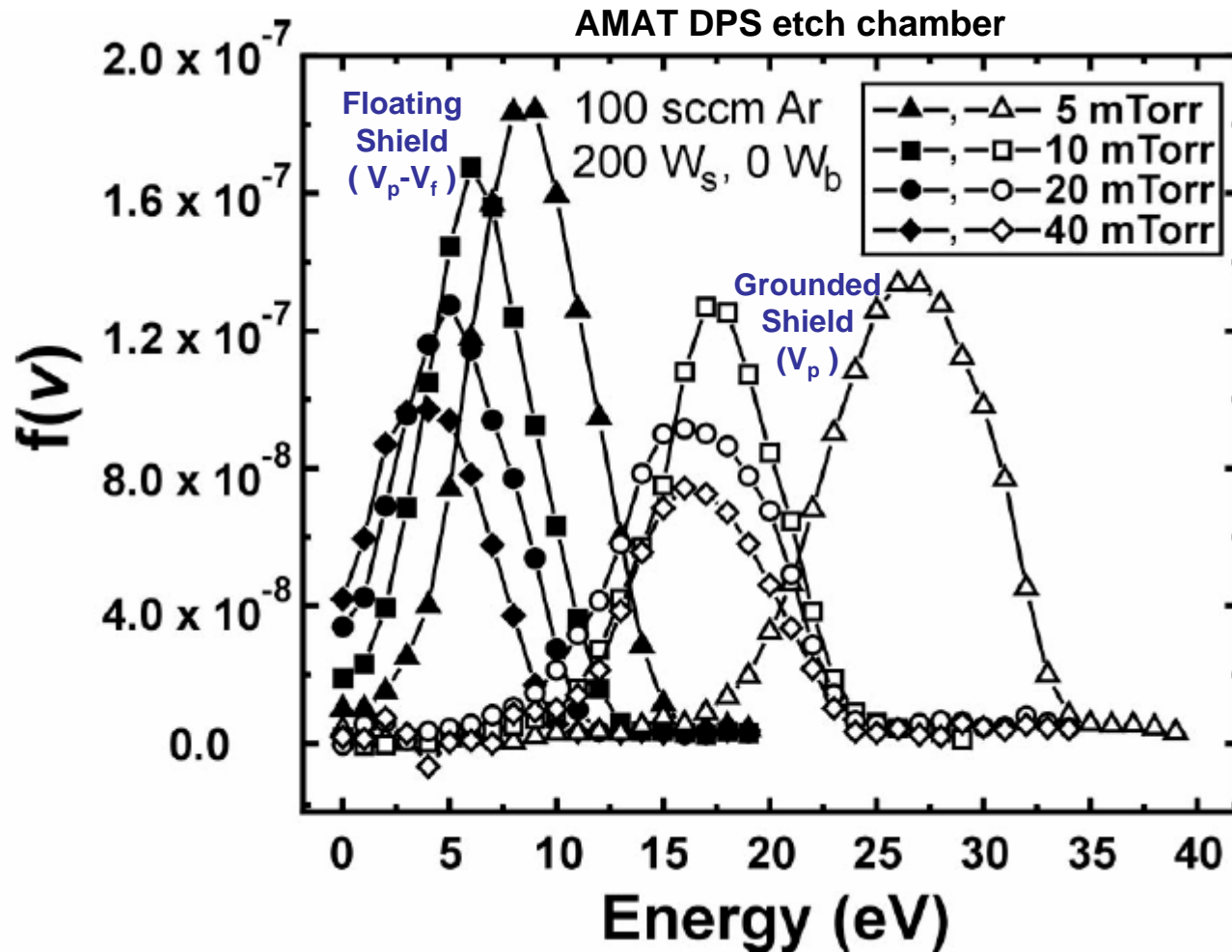
Inductively coupled  
plasma



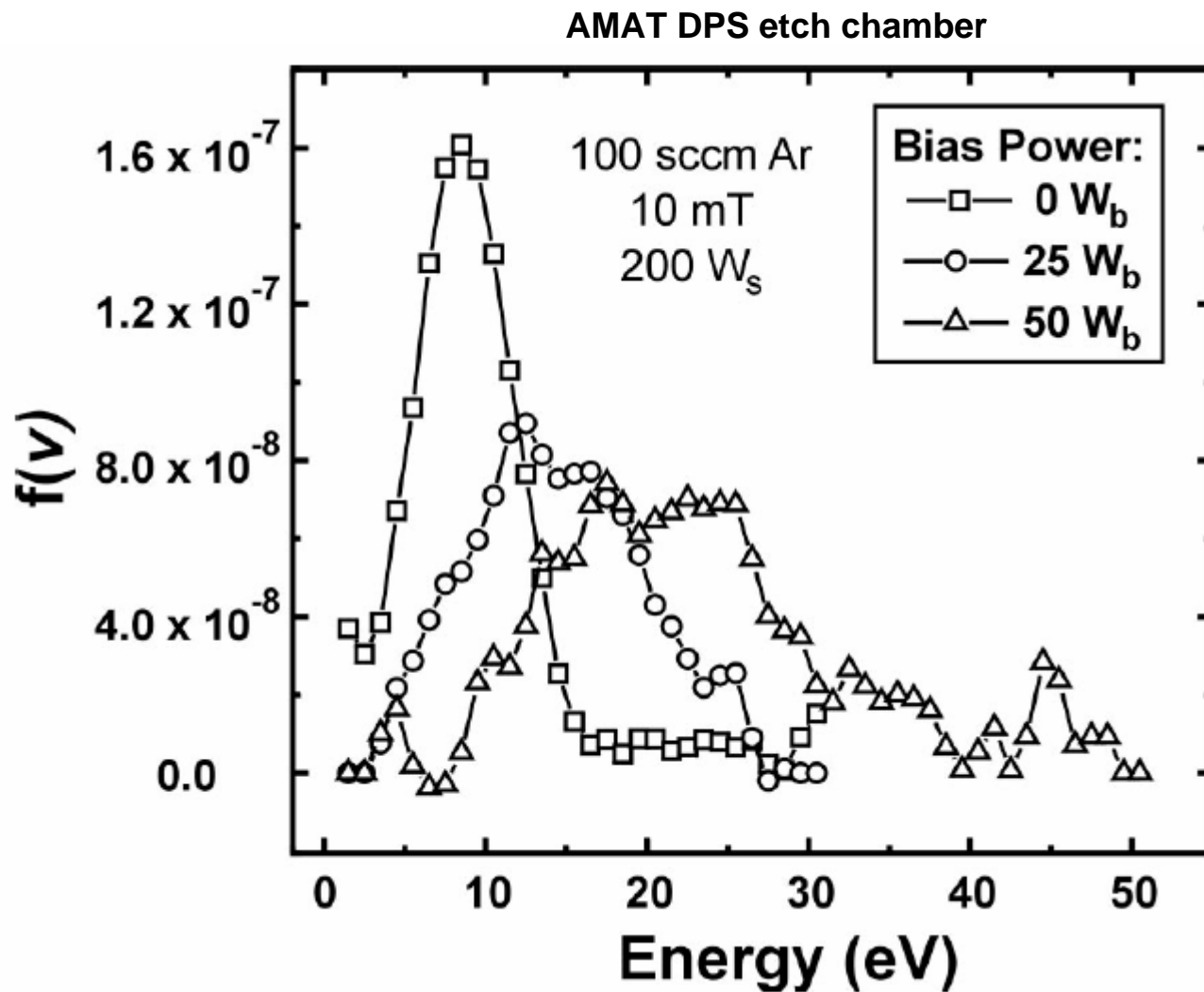
# Ion energy distribution vs. pressure



# Ion energy distribution vs. pressure

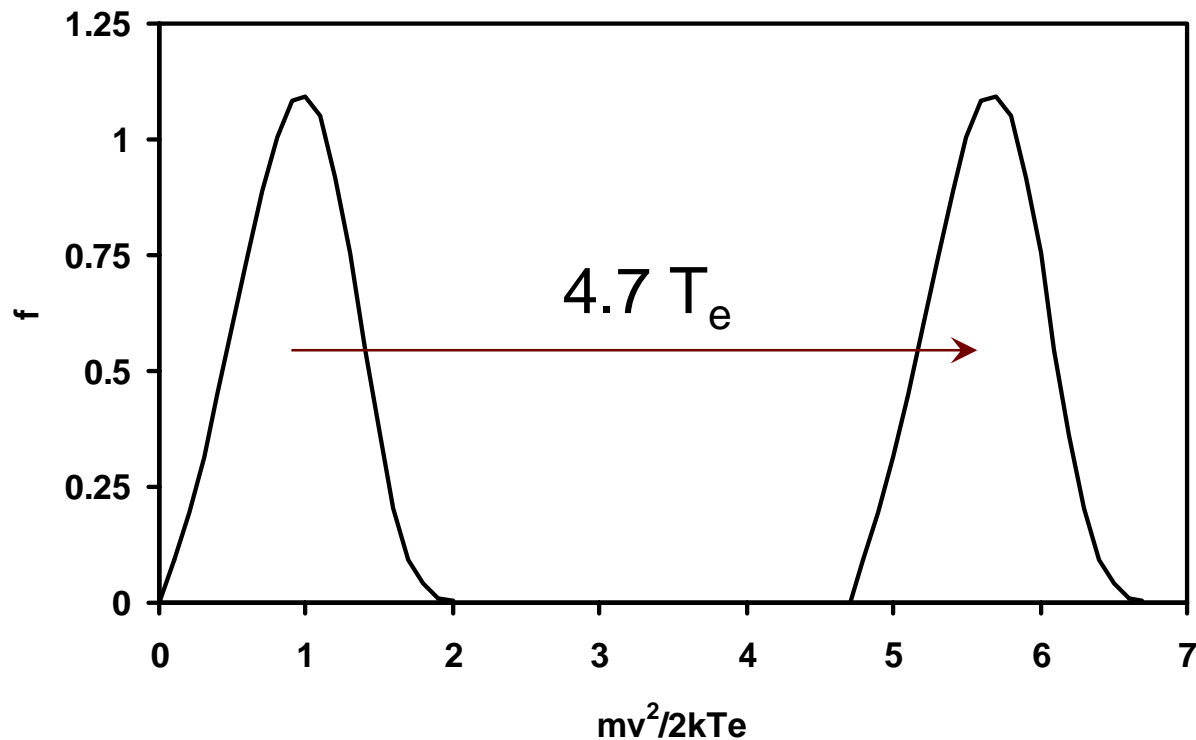


# Ion energy distribution vs. RF bias

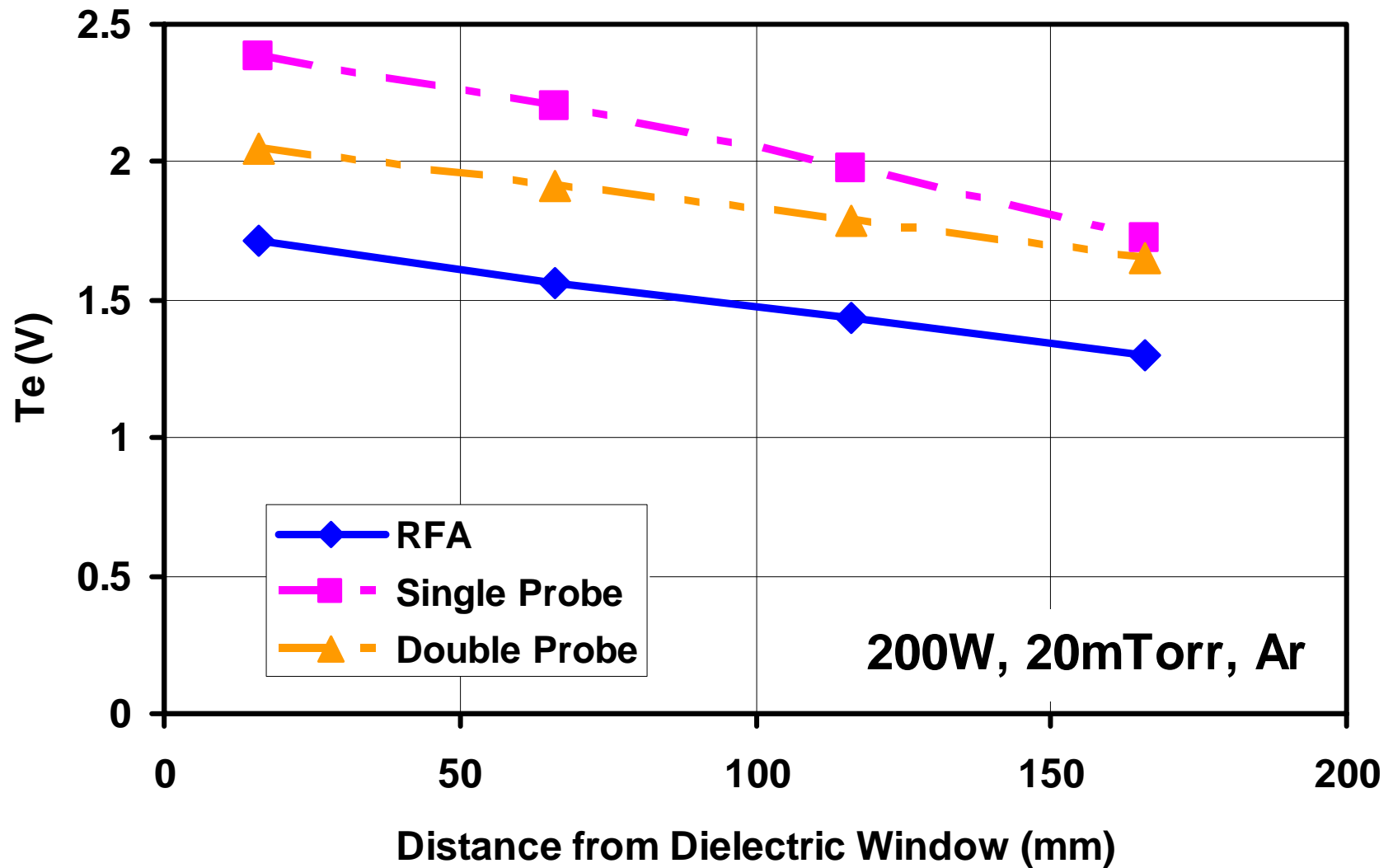


# Inferred $T_e$ from I.E.D.

- Model assumes that the ion energy distribution is developed in the presheath, then ions are uniformly accelerated across a collisionless sheath. [K.U. Riemann, Phys Fluids 24(12), 1981.]
- Peak ion energy predicted at  $5.7 T_e$ .



# $T_e$ from IEA vs. Langmuir probe



# IED in a Pulsed Plasma

Bauer, et. al.

## Process conditions:

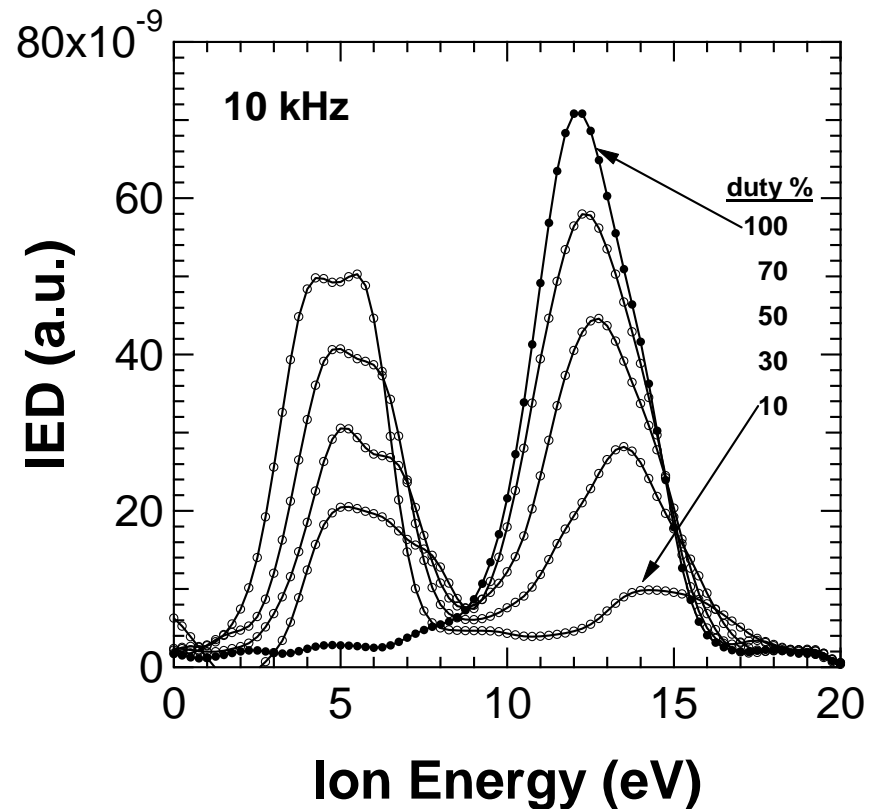
Inductively coupled plasma  
source

10 kHz pulse rate, various duty  
cycles.

150 W time-averaged source  
power.

10 mTorr N<sub>2</sub>

With reduced duty cycle,  
the population of high-  
energy ions decreases and  
low-energy ions increases.



# Conclusions and Comments

- The micro-fabricated IEA worked as expected.
- Ion energy distribution is determined by the presheath.
- $T_e$  trends agreed qualitatively with Langmuir probes.
- Fabrication used standard MEMS operations, although we did not use the standard SUMMiT™ lot flow.
- It took several iterations to correct process and operational issues. There are 7 mask levels and ~120 process steps.
- Packaging is important. The goal was for the IEA to be a plug-in part. A lot of time was spent on making holders, epoxy packages, and improving leads.





# General Comments for the MDL Facility

- MDL processes are rigorously controlled, for delivery of radiation hard IC's and MEMS parts.
  - You get what you ask for.
  - With 10's of products in the line at a given time, it is important that they don't affect each other.
- Material choices must be compatible with silicon CMOS.
  - Conductors: Al, W, Ti, TiN, poly-Si
  - Insulators: SiO<sub>2</sub>, SiN, AlN, SiON
  - Other materials (Ni, Au, Pt) available at post processing.
- There are limitations on device size and thickness.





## Microelectronics Development Laboratory (MDL)